

SKiiP26GB12F4V1

Features

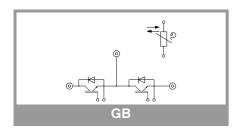
- Fast Trench 4 IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to T_{C} = 125°C
- Product reliability results valid for T_j≤150°C (recommended T_{j,op}=-40...+150°C)

Absolute	Maximum Ratin	igs		
Symbol	Conditions		Values	Unit
Inverter -	IGBT			
V _{CES}	T _j = 25 °C		1200	V
Ic	T _j = 175 °C	T _s = 25 °C	202	Α
		T _s = 70 °C	164	Α
I _{Cnom}			200	А
I _{CRM}	$I_{CRM} = 2 \times I_{Cnom}$		400	А
V_{GES}			-20 20	V
t _{psc}	$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T _j = 150 °C	10	μѕ
Tj			-40 175	°C
Inverse -	Diode			
I _F	T _j = 175 °C	T _s = 25 °C	194	Α
		T _s = 70 °C	154	Α
I _{Fnom}			200	Α
I _{FRM}	I _{FRM} = 3 x I _{Fnom}		600	Α
I _{FSM}	10 ms, sin 180°, T _j = 150 °C		990	А
Tj			-40 175	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C, 20 A per spring		200	Α
T _{stg}			-40 125	°C
V _{isol}	AC sinus 50 Hz,	t = 1 min	2500	V

Characte	eristics					
Symbol	Conditions	min.	typ.	max.	Unit	
Inverter -	IGBT		•			
V _{CE(sat)}	I _C = 200 A	T _j = 25 °C		2.05	2.40	V
	V _{GE} = 15 V chiplevel	T _j = 150 °C		2.50	2.85	V
V _{CE0}	chiplevel	T _j = 25 °C		0.80	0.90	V
		T _j = 150 °C		0.70	0.80	V
r _{CE}	V _{GE} = 15 V chiplevel	T _j = 25 °C		6.3	7.5	mΩ
		T _j = 150 °C		9.0	10	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_{C} = 7.6 \text{ r}$	mA	5.2	5.8	6.4	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C		0.1	0.3	mA
	V _{CE} = 1200 V			-		mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		12.30		nF
C _{oes}		f = 1 MHz				nF
C _{res}		f = 1 MHz		0.69		nF
Q _G	- 8 V+ 15 V			1130		nC
R _{Gint}	T _j = 25 °C			3.8		Ω
t _{d(on)}	$\begin{aligned} &V_{CC}=600 \text{ V} \\ &I_{C}=200 \text{ A} \\ &R_{G \text{ on}}=2 \Omega \\ &R_{G \text{ off}}=2 \Omega \\ &\text{di/dt}_{on}=4100 \text{ A/}\mu\text{s} \\ &\text{di/dt}_{off}=2500 \text{ A/}\mu\text{s} \end{aligned}$	T _j = 150 °C		167		ns
t _r		T _j = 150 °C		52		ns
Eon		T _j = 150 °C		16.8		mJ
t _{d(off)}		T _j = 150 °C		414		ns
t _f		T _j = 150 °C		52		ns
E _{off}	V _{GE} = +15/-15 V	T _j = 150 °C		16.3		mJ
R _{th(j-s)}	per IGBT, λ _{paste} =0.8 W/(Km)			0.25		K/W





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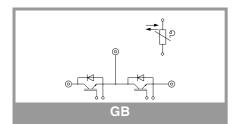
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Characteristics								
Symbol	Conditions		min.	typ.	max.	Unit		
Inverse - Diode								
$V_F = V_{EC}$	I _F = 200 A	T _j = 25 °C		2.20	2.52	V		
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.15	2.47	V		
V_{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V		
	Criipievei	T _j = 150 °C		0.90	1.10	V		
r _F	ahinlayal	T _j = 25 °C		4.5	5.1	mΩ		
	chiplevel	T _j = 150 °C		6.3	6.9	mΩ		
I _{RRM}	$di/dt_{off} = 3840 \text{ A/}\mu\text{s}$ $V_{GE} = -15 \text{ V}$	T _j = 150 °C		189		Α		
Q _{rr}		T _j = 150 °C		28.7		μC		
E _{rr}		T _j = 150 °C		11.7		mJ		
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(K*m)			0.34		K/W		
Module								
L _{CE}				20		nH		
Ms	to heat sink		2		2.5	Nm		
W				50		g		
Temperat	ure Sensor					_		
R ₁₀₀	$T_c=100^{\circ}C (R_{25}=5 k\Omega)$		493 ± 5%			Ω		
B _{25/85}	$R_{(T)}=R_{25}*exp[B_{25/85}*(1/T-1/298)], [T]=K$			3420		K		



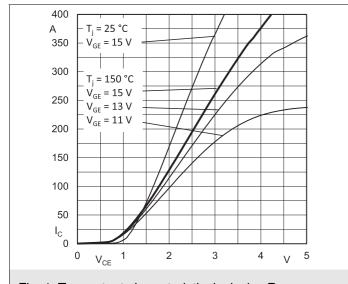


Fig. 1: Typ. output characteristic, inclusive $R_{\text{CC'+}\,\text{EE'}}$

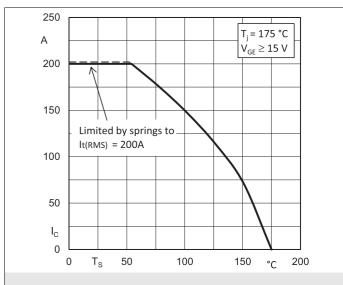


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

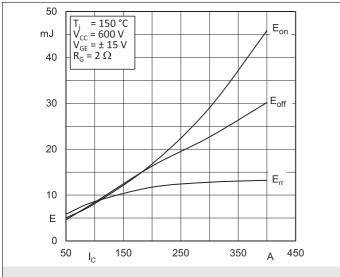


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

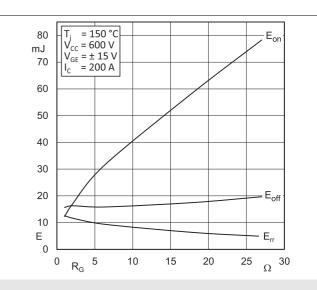


Fig. 4: Typ. turn-on /-off energy = f (R_G)

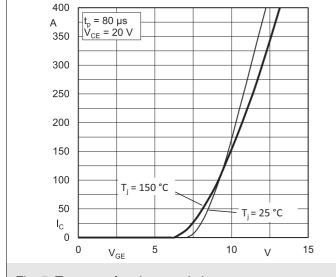


Fig. 5: Typ. transfer characteristic

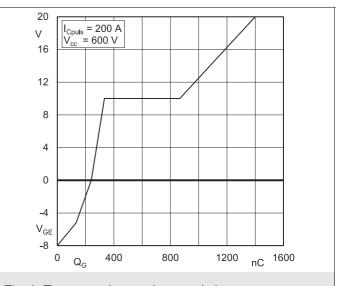
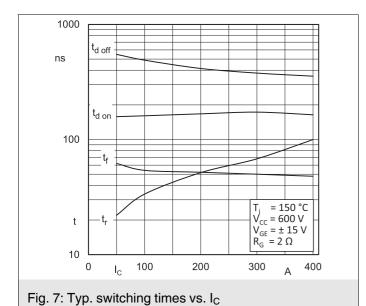
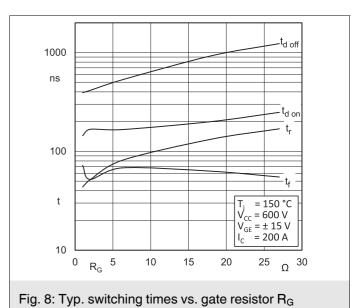
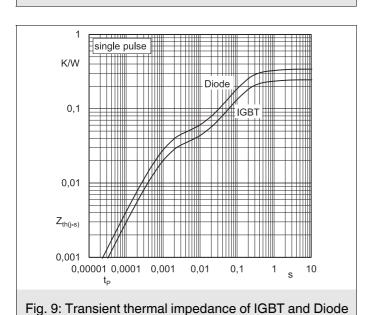
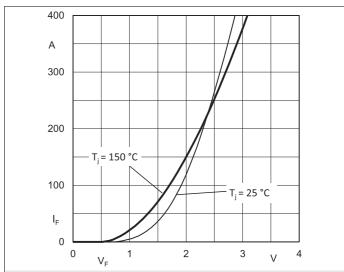


Fig. 6: Typ. gate charge characteristic









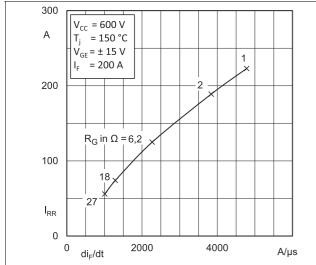


Fig. 10: Typ. CAL diode forward charact., incl. R_{CC'+ EE'}

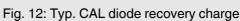
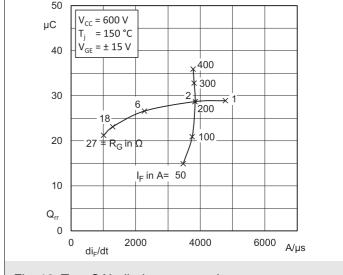
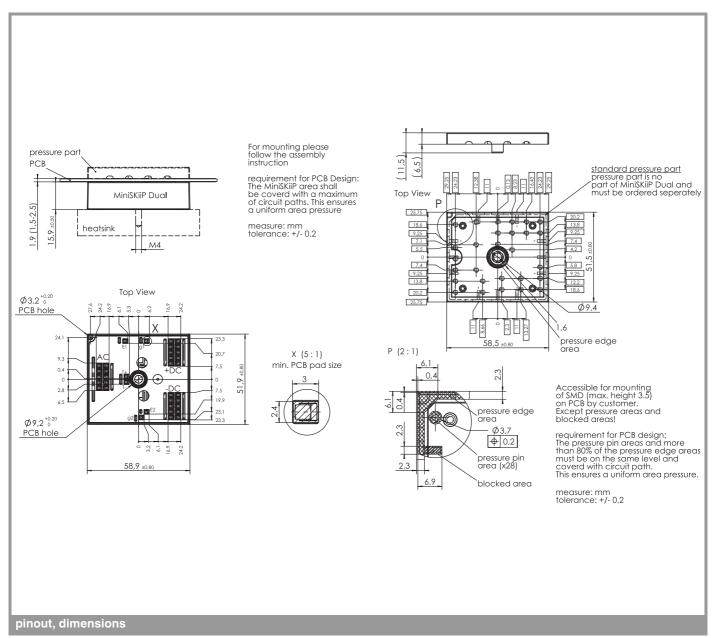
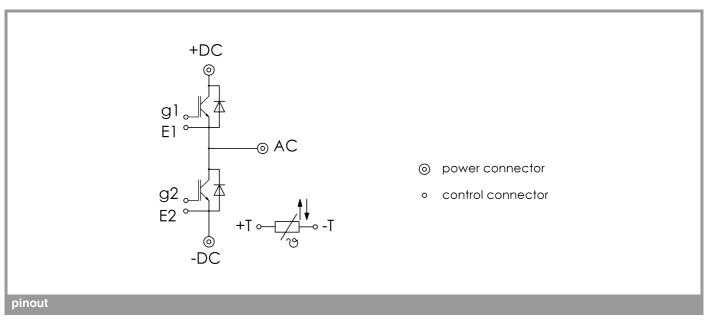


Fig. 11: Typ. CAL diode peak reverse recovery current







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

*IMPORTANT INFORMATION AND WARNINGS

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